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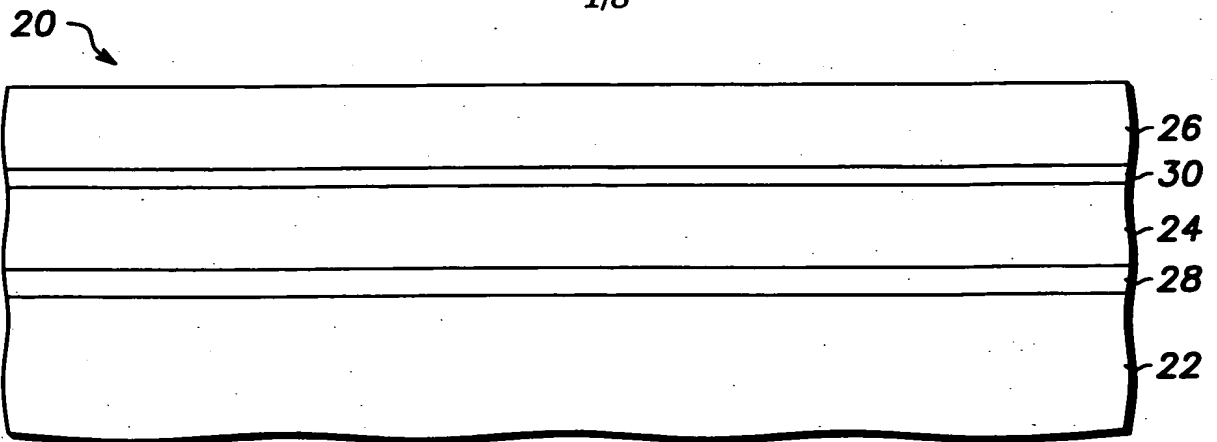
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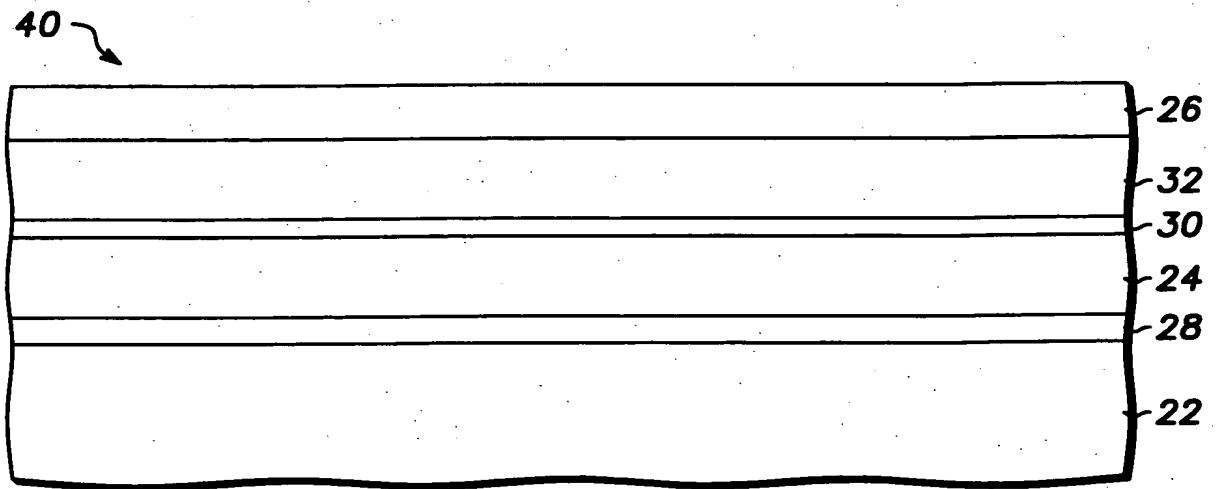
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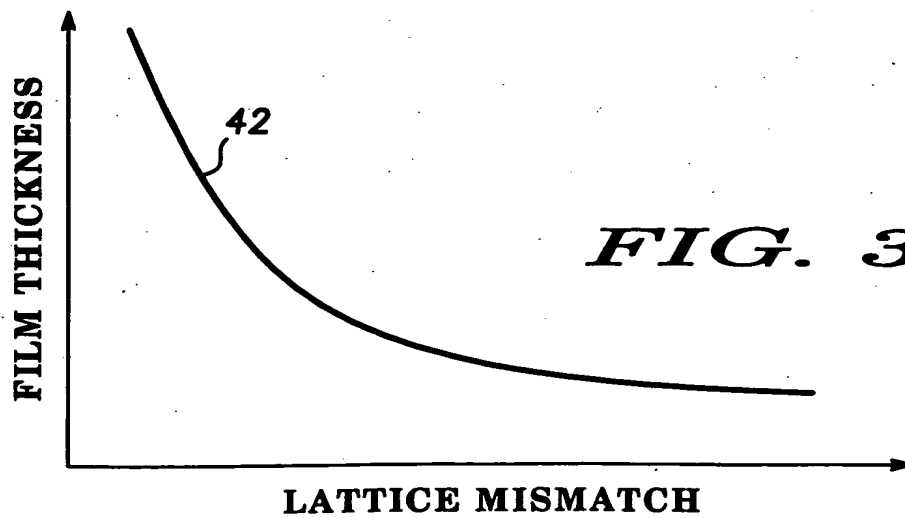
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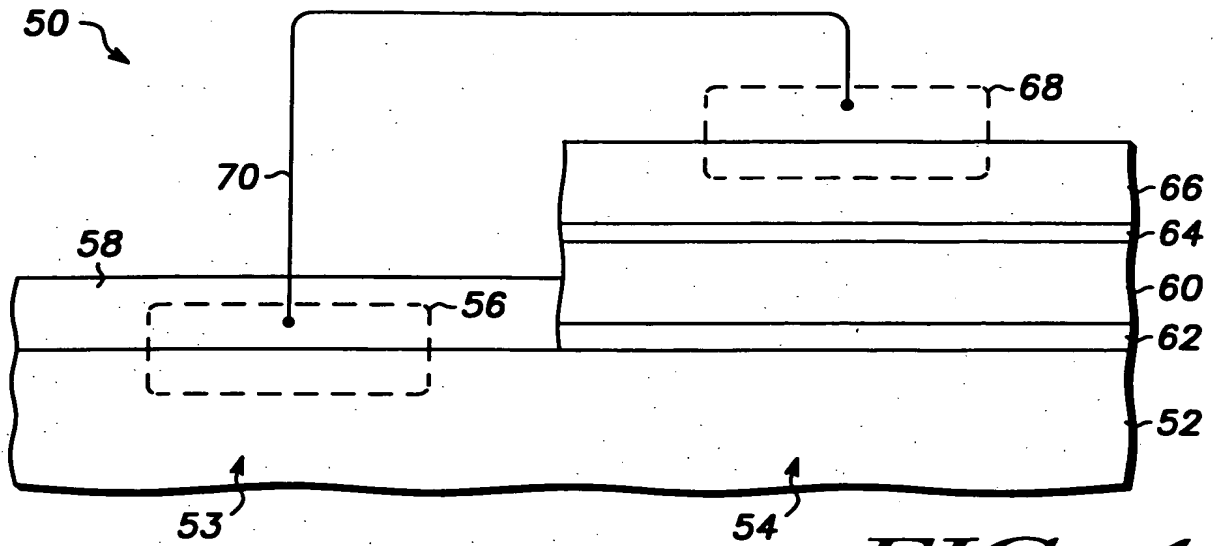
**FIG. 1**



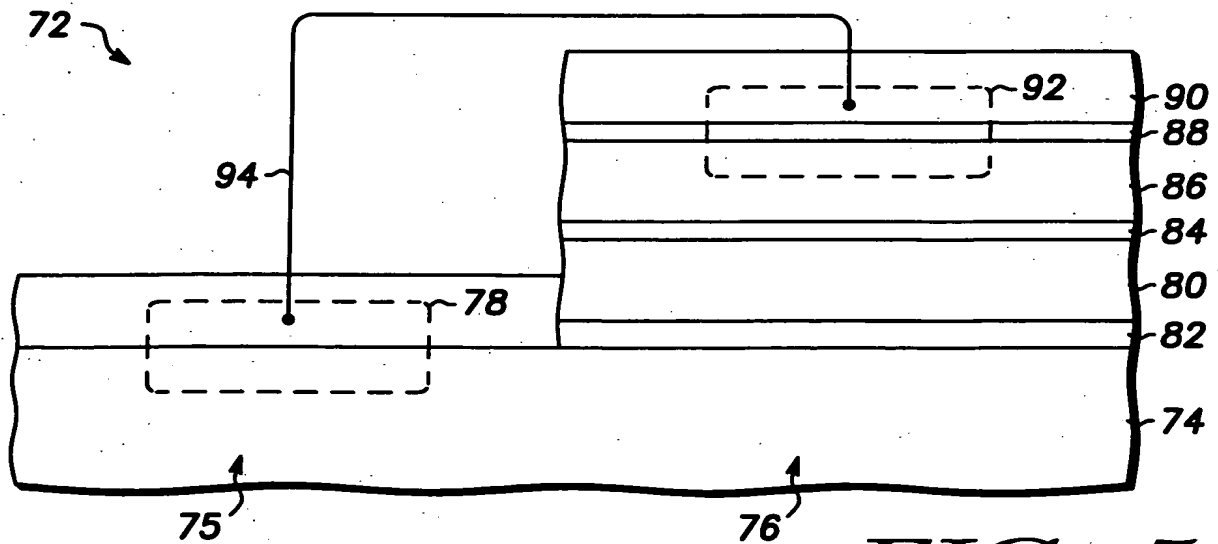
**FIG. 2**



**FIG. 3**

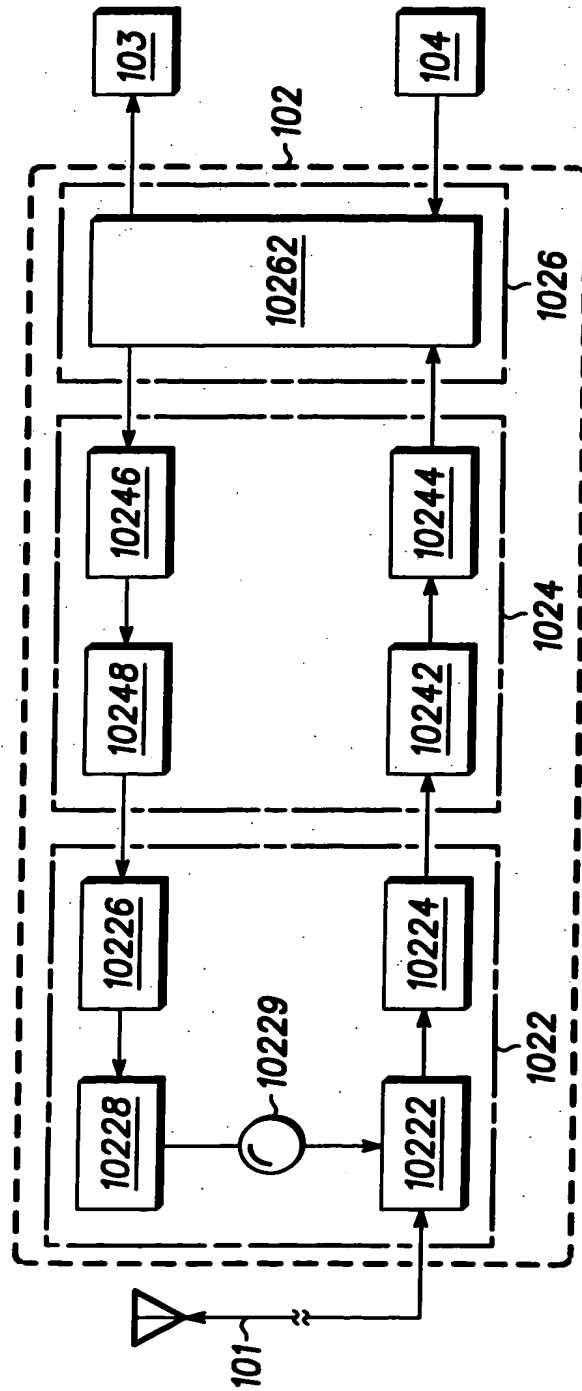


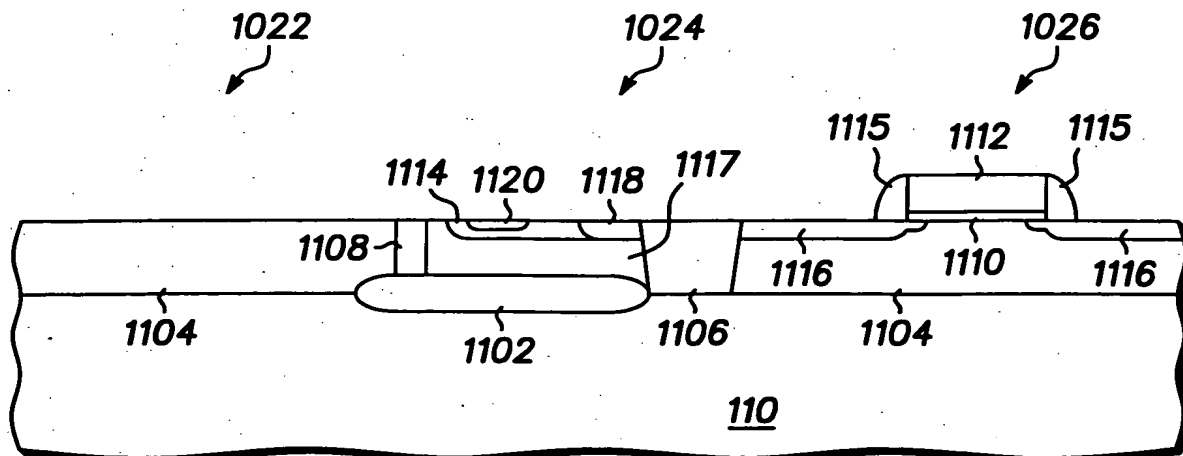
**FIG. 4**



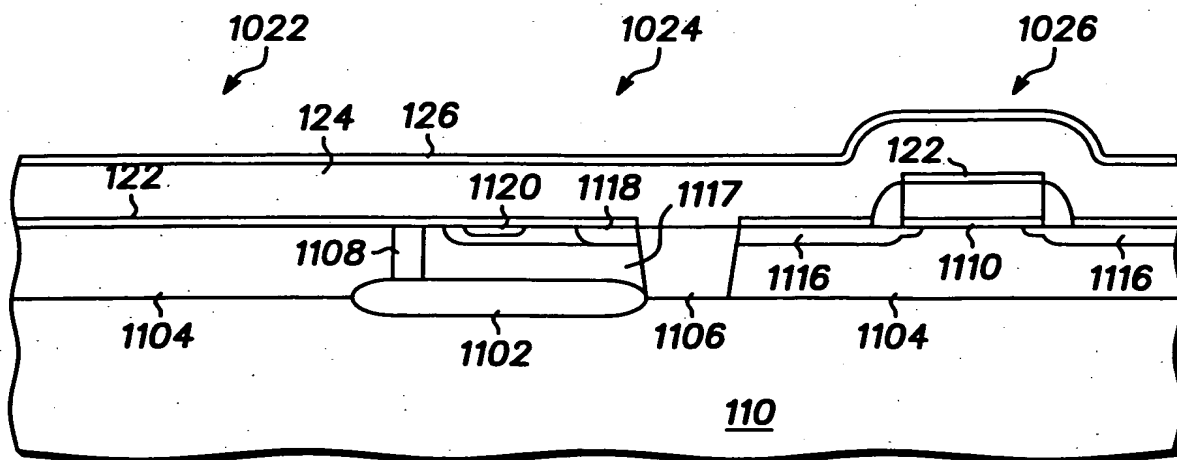
**FIG. 5**

FIG. 6  
100

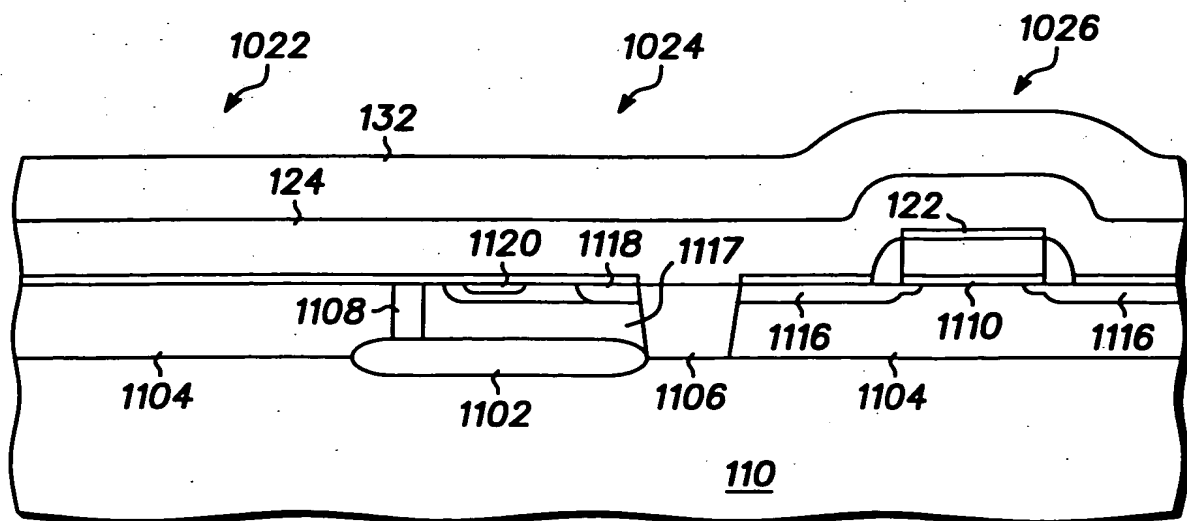




102 **FIG. 7**



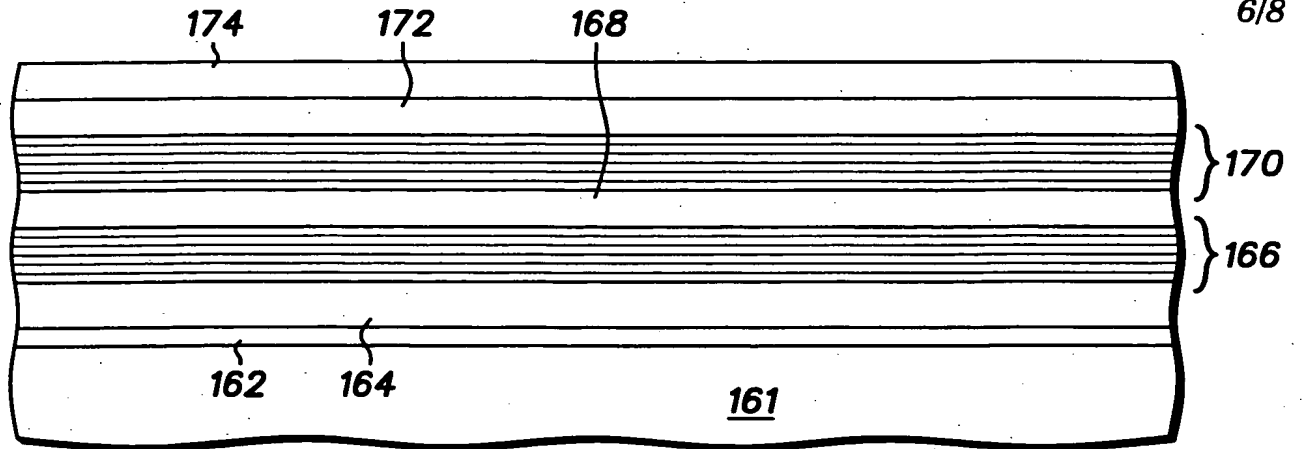
102 **FIG. 8**



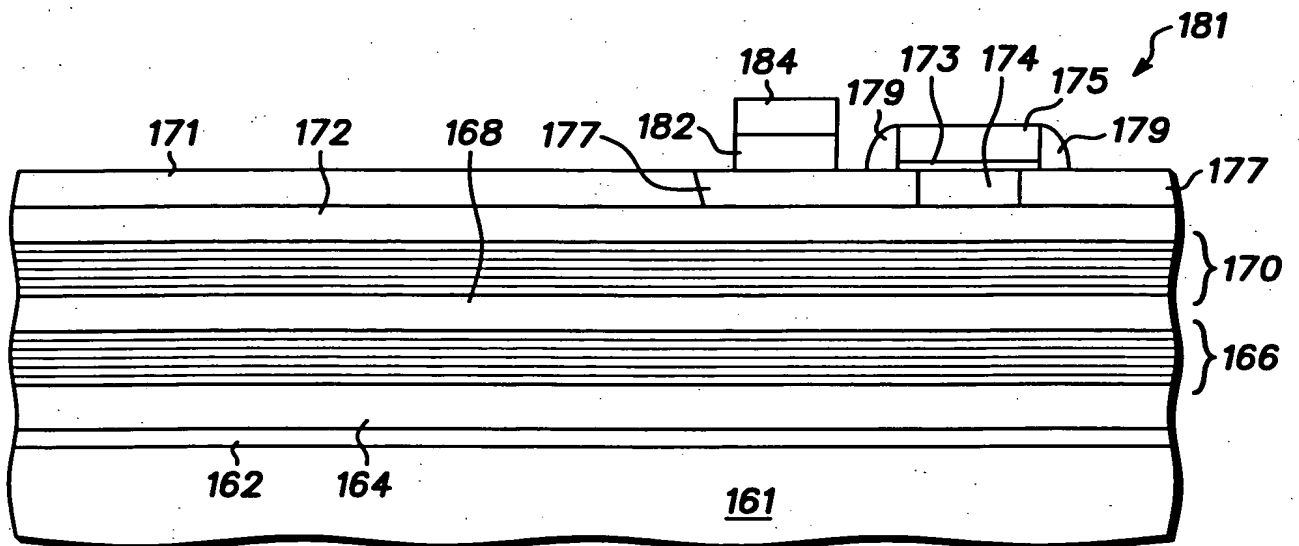
102 **FIG. 9**

This cross-sectional view shows a semiconductor device with a substrate 110. A base layer 1104 is formed on the substrate. On the base layer, there are several components: a central structure 1102, and two side structures 1106. The central structure 1102 includes a layer 1108 and a top layer 152. The side structures 1106 include a layer 1110 and a top layer 152. The device is covered by a top layer 156. Various other layers and features are labeled with numbers 1022, 1024, 1026, 154, 152, 1562, 1564, 1566, 142, 132, 124, 122, and 142.

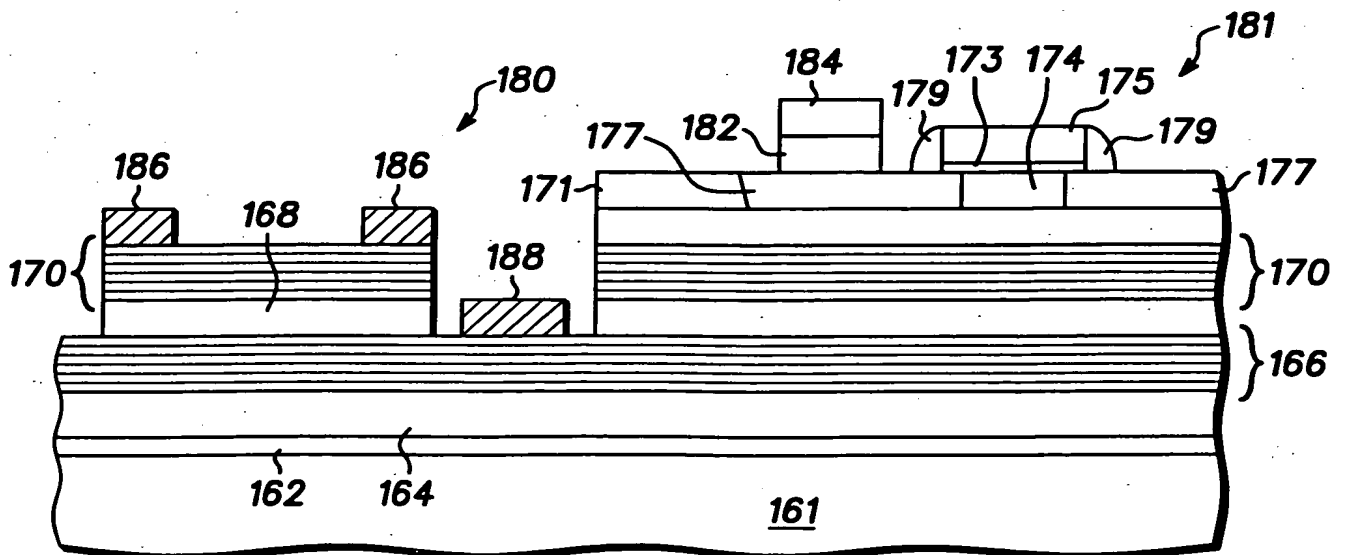
102 **FIG. 11**



160 **FIG. 12**



160 **FIG. 13**

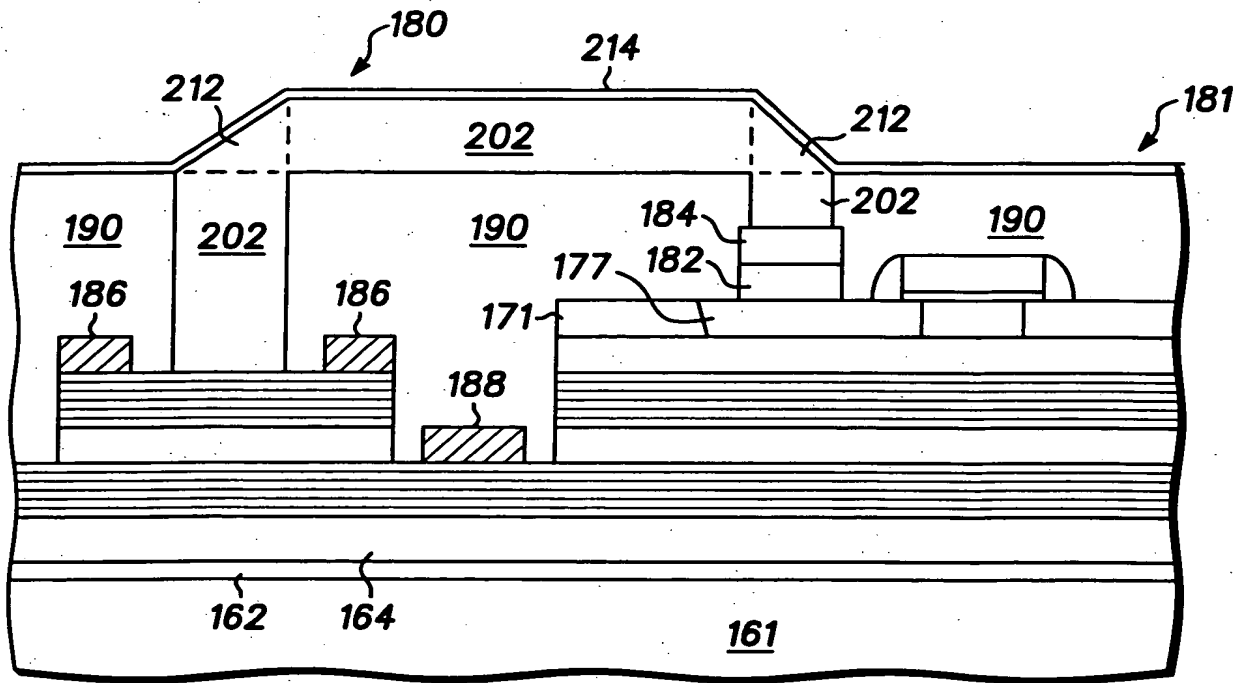
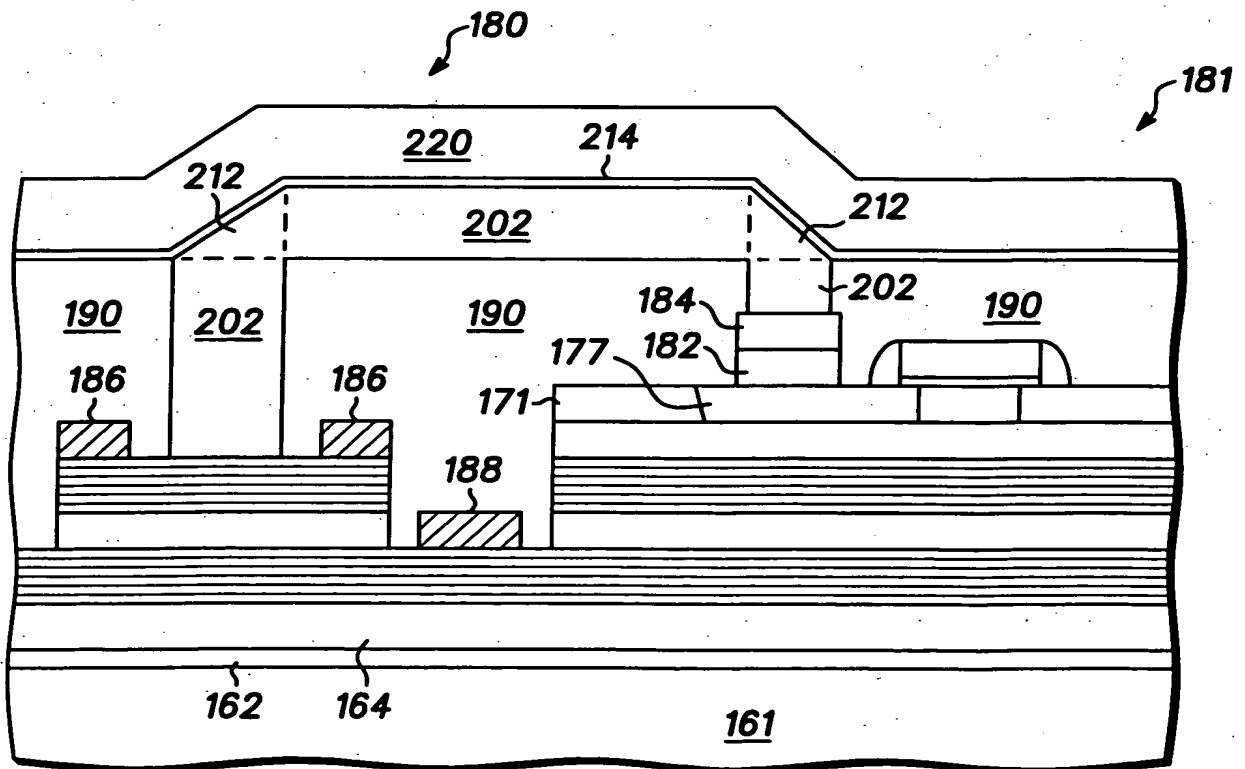


160 **FIG. 14**



**FIG. 16**



**FIG. 17****FIG. 18**